KMB035N40DB

N-Ch Trench MOSFET

General Description

This Trench MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for Back-light Inverter and Power Supply.

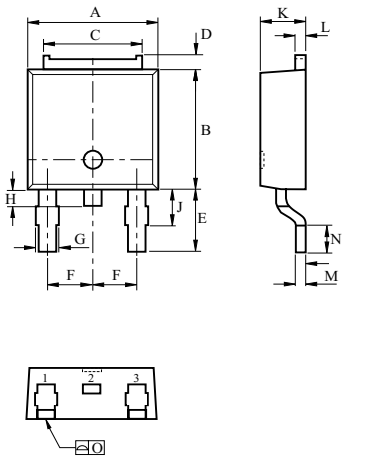
FEATURES

· V_{DSS}=40V, I_D=35A.

· Low Drain to Source On-state Resistance.

: $R_{DS(ON)}$=12.0mΩ(Max.) @ V_{GS}=10V

: $R_{DS(ON)}$=17.0mΩ(Max.) @ V_{GS}=4.5V



DIM	MILLIMETERS
A	6.60±0.20
B	6.10±0.20
C	5.34±0.30
D	0.70±0.20
E	2.70±0.15
F	2.30±0.10
G	0.96 MAX
H	0.90 MAX
J	1.80±0.20
K	2.30±0.10
L	0.50±0.10
M	0.50±0.10
N	0.70 MIN
O	Max 0.1

DPAK (1)

* Weight : 0.33g(typ)

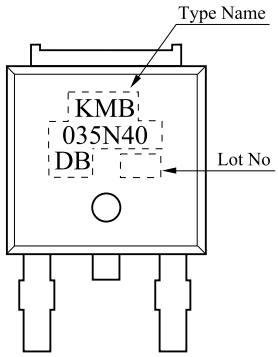
MAXIMUM RATING (Ta=25℃ Unless otherwise Noted)

CHARACTERISTIC		SYMBOL	N-Ch	UNIT
Drain to Source Voltage		V_{DSS}	40	V
Gate to Source Voltage		V_{GSS}	±20	V
Drain Current	DC@T_C=25℃ (Note1)	I_D	35	A
	Pulsed (Note2)	I_{DP}	140	
Drain Power Dissipation	@T_C=25℃ (Note1)	P_D	43	W
	@Ta=25℃ (Note2)		3.1	
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 150	℃
Thermal Resistance, Junction to Case (Note1)		R_{thJC}	2.9	℃/W
Thermal Resistance, Junction to Ambient (Note2)		R_{thJA}	40	℃/W

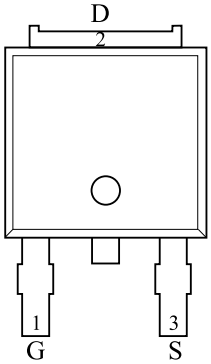
Note 1) R_{thJC} means that the infinite heat sink is mounted.

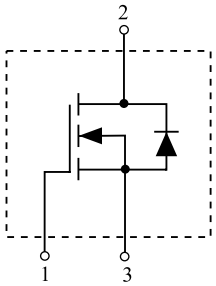
Note 2) Surface Mounted on 1 ×1 Pad of 2 oz copper.

Marking



PIN CONNECTION (TOP VIEW)





ELECTRICAL CHARACTERISTICS (Ta = 25℃**)**

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static							
Drain to Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250 μA	40	-	-	V
Drain Cut-off Current		I_{DSS}	V_{GS}=0V, V_{DS}=32V	-	-	1	μA
Gate to Source Leakage Current		I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Gate to Source Threshold Voltage		V_{th}	V_{DS}=V_{GS}, I_D=250 μA	1.7	-	3.0	V
Drain to Source On Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=18A (Note3)	-	8.0	12.0	mΩ
			V_{GS}=4.5V, I_D=16A (Note3)	-	13.0	17.0	
Forward Transconductance		g_{fs}	V_{DS}=5V, I_D=18A (Note3)	-	48	-	S
Dynamic							
Input Capacitance		C_{iss}	V_{DS}=20V, f=1MHz, V_{GS}=0V	-	970	-	pF
Ouput Capacitance		C_{oss}		-	205	-	
Reverse Transfer Capacitance		C_{rss}		-	100	-	
Gate Resistance		R_g	f=1MHz	-	2.9	-	Ω
Total Gate Charge	V_{GS}=10V	Q_g	V_{DS}=20V, V_{GS}=10V, I_D=18A (Note3)	-	20.2	-	nC
	V_{GS}=5V	Q_g		-	10.7	-	
Gate to Source Charge		Q_{gs}		-	5.1	-	
Gate to Drain Charge		Q_{gd}		-	4.6	-	
Turn-On Delay Time		$t_{d(on)}$	V_{DD}=20V, V_{GS}=10V, I_D=18A, R_G=6Ω (Note3)	-	18	-	ns
Turn-On Rise Time		t_r		-	17	-	
Turn-Off Delay Time		$t_{d(off)}$		-	55	-	
Turn-Off Fall Time		t_f		-	13	-	
Source-Drain Diode Ratings							
Continuous Source Current		I_S	-	-	35	-	A
Pulsed Source Current		I_{SP}	-	-	140	-	A
Source to Drain Forward Voltage		V_{SD}	V_{GS}=0V, I_S=3A (Note3)	-	0.8	1.2	V
Reverse Recovery time		t_{rr}	I_S=18A, dI/dt=100A/ μs	-	24	-	ns
Reverse Recovered Charge		Q_{rr}	I_S=18A, dI/dt=100A/ μs	-	8.8	-	nC
Note3) Pulse Test : Pulse width <300μs , Duty cycle < 2%							

Fig1. I_D - V_{DS}

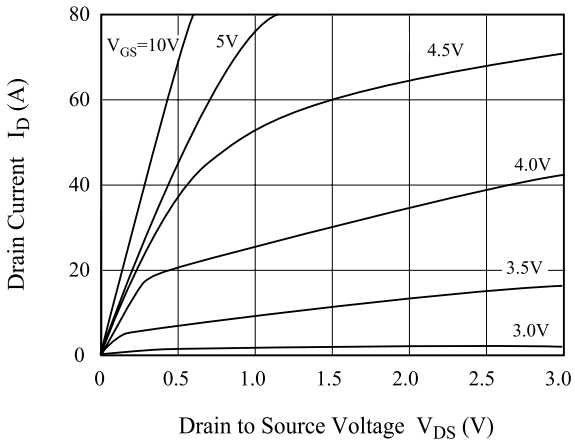


Fig2. $R_{DS(on)}$ - I_D

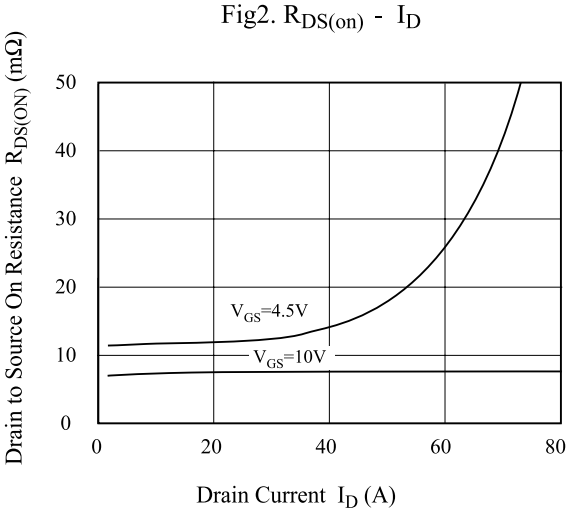


Fig3. I_D - V_{GS}

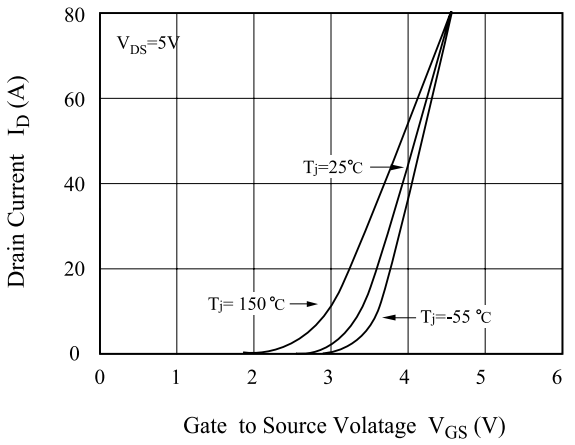


Fig4. $R_{DS(on)}$ - T_j

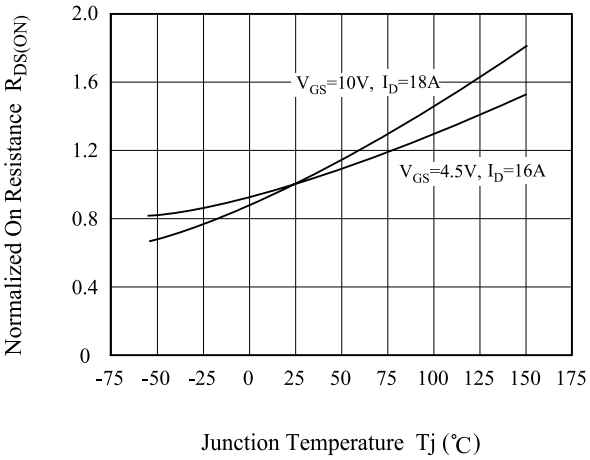


Fig5. V_{th} - T_j

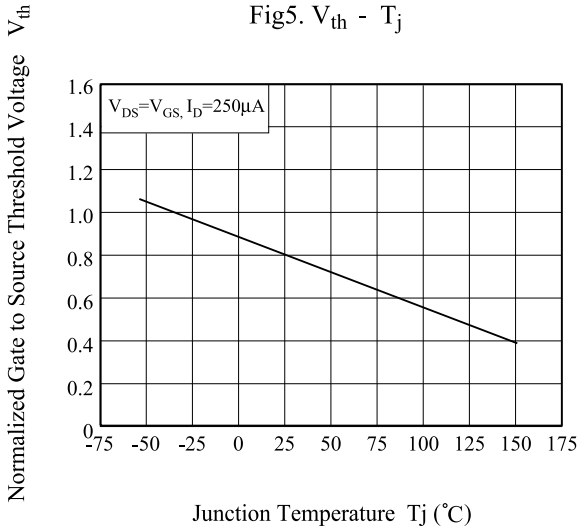


Fig6. I_S - V_{SD}

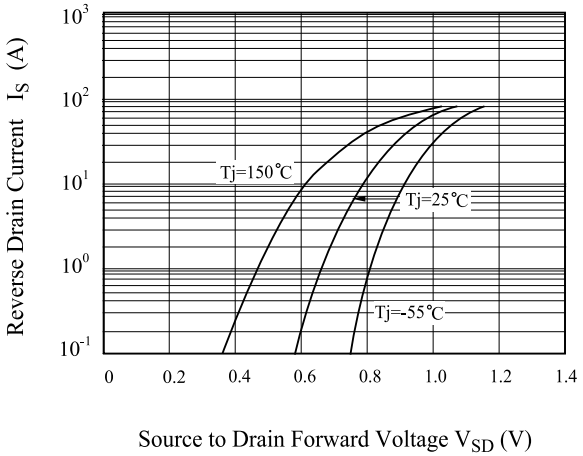


Fig7. $R_{DS(on)}$ - V_{GS}

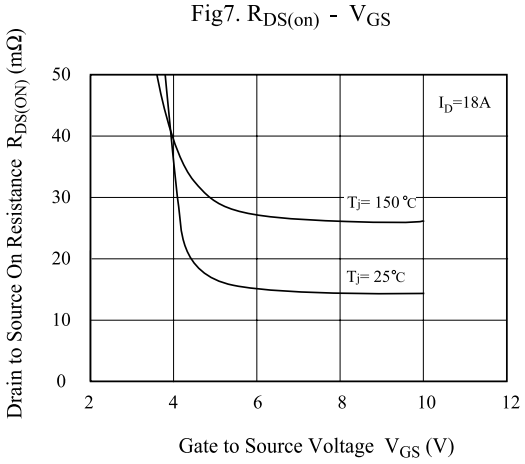


Fig 8. C - V_{DS}

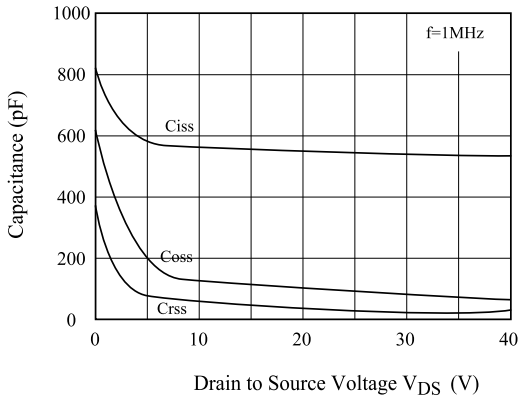


Fig 9. V_{GS} - Q_g

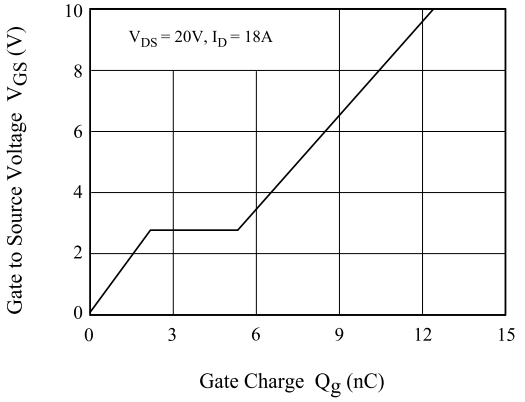


Fig10. Safe Operation Area

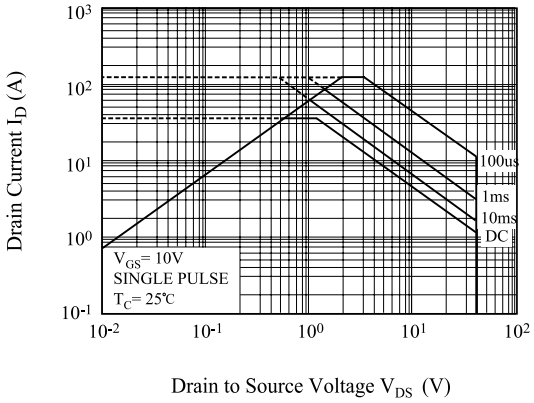
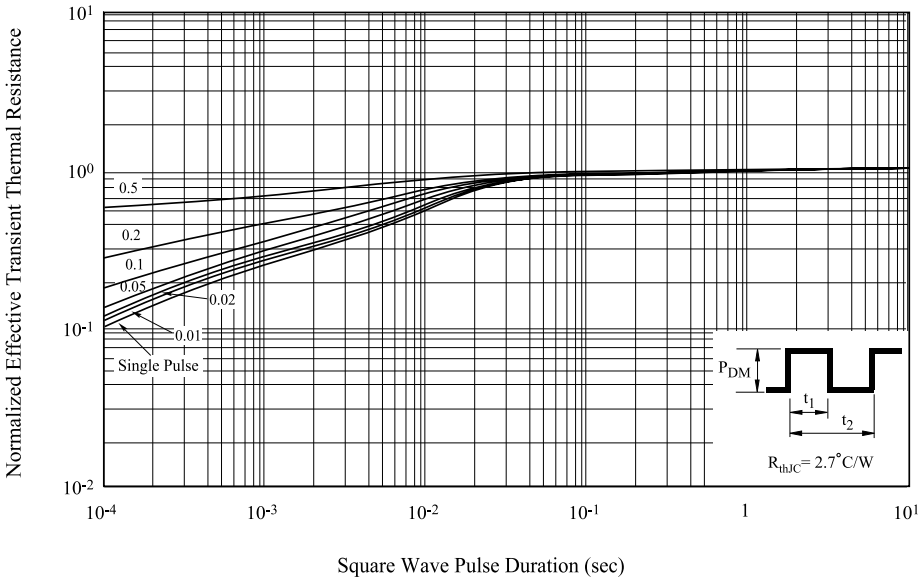



Fig11. Transient Thermal Response Curve